

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

MANABE et al.

Divisional of Appln. No. 09/379,621

Group Art Unit: 2811

Filed: Herewith

Examiner: M. Tran

Title: LIGHT-EMITTING SEMICONDUCTOR  
DEVICE USING GROUP III NITRIDE COMPOUND (AS AMENDED)

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February 15, 2001

PRELIMINARY AMENDMENT

Hon. Commissioner of Patents  
Washington, D.C.

Dear Sir:

Prior to the examination, please amend the above-identified application as follows:

IN THE TITLE:

Please change the title of the invention to --LIGHT-EMITTING ALUMINUM GALLIUM  
INDIUM NITRIDE COMPOUND SEMICONDUCTOR DEVICE HAVING AN IMPROVED  
LUMINOUS INTENSITY--.

IN THE CLAIMS:

Please cancel claims 1-15 without prejudice or disclaimer.

Please add new claims 16 and 17 as follows:

- 131 SUB FI
- 16. A method for producing a light-emitting semiconductor device, said method comprising:
- forming a substrate;
  - forming a buffer layer on said substrate;
  - forming an N-layer of N-type nitrogen-III Group compound semiconductor satisfying the formula  $Al_xGa_yIn_{1-x-y}N$ , inclusive of  $x=0, y=0$  and  $x=y=0$ ;